

#### Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

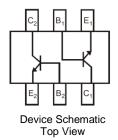
#### **Mechanical Data**

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish; Solderable per MIL-STD-202, Method 208<sup>(2)</sup>
- Weight: 0.006 grams (Approximate)

875

SOT363

Top View



#### Ordering Information (Note 4)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMDT3904-7-F	Active	AEC-Q101	K6N	7	8	3,000

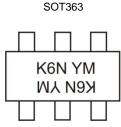
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



K6N = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: D = 2016) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н			J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code			-		-	-	-	0	0	0	NI	D



### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6.0	V
Collector Current	Ιc	200	mA

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	625	°C/W
Operating and Storage and Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

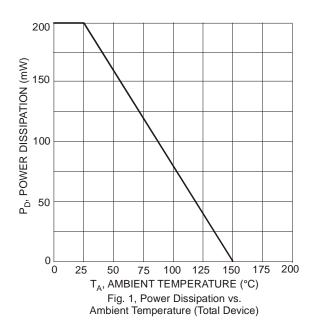
### ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

# Thermal Characteristic and Derating Information





# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

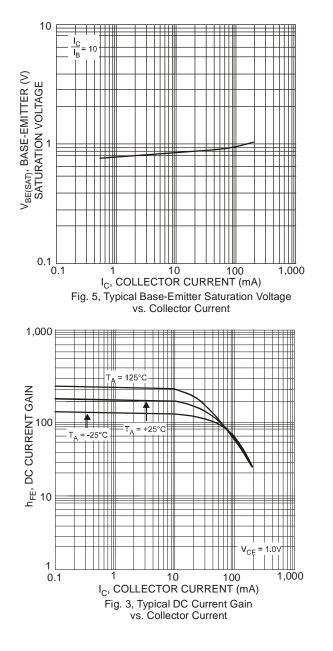
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS					
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60		V	$I_{\rm C} = 100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 7)	BV <sub>CEO</sub>	40		V	$I_{\rm C} = 10.0 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6.0	_	V	$I_E = 100 \mu A$ , $I_C = 0$
Collector-Base Cut-Off Current	I <sub>CBO</sub>	_	50	nA	$V_{CB} = 50V$
Collector-Emitter Cut-Off Current			50	nA	$V_{CE} = 40V, V_{BE(OFF)} = 3.0V$
	ICEV	_	50	ПА	$V_{CE} = 40V, V_{BE(ON)} = 0.25V$
Emitter-Base Cut-Off Current	I <sub>EBO</sub>		50	nA	$V_{EB} = 5V$
ON CHARACTERISTICS (Note 7)					
		40	—		$I_{C} = 100 \mu A, V_{CE} = 1.0 V$
		70	—		$I_{C} = 1.0 \text{mA}, V_{CE} = 1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	100	300		$I_{C} = 10 \text{mA}, V_{CE} = 1.0 \text{V}$
		60 30	_		$I_{C} = 50 \text{mA}, V_{CE} = 1.0 \text{V}$
		30			$I_{C} = 100 \text{mA}, V_{CE} = 1.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		0.20 0.30	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 1.0 {\rm mA}$
	02(00)				$I_C = 50$ mA, $I_B = 5.0$ mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	0.65	0.85	V	$I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 1.0 {\rm mA}$
SMALL SIGNAL CHARACTERISTICS	()		0.95		$I_{\rm C} = 50 {\rm mA}, I_{\rm B} = 5.0 {\rm mA}$
Output Capacitance			4.0	pF	V <sub>CB</sub> = 5.0V, f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>obo</sub> C <sub>ibo</sub>		4.0 8.0	pF	$V_{CB} = 5.0V, T = 1.0MHz, T_E = 0$ $V_{EB} = 0.5V, f = 1.0MHz, T_C = 0$
Input Impedance		1.0	10	μ kΩ	$V_{EB} = 0.5V, I = 1.0WHZ, IC = 0$
Voltage Feedback Ratio	h <sub>ie</sub>	0.5	8.0	x 10 <sup>-4</sup>	
Small Signal Current Gain	h <sub>re</sub> h <sub>fe</sub>	100	400		V <sub>CE</sub> = 10V, I <sub>C</sub> = 1.0mA, f = 1.0kHz
Output Admittance		1.0	400	 μS	1 - 1.0012
· · ·	h <sub>oe</sub>		40		V <sub>CE</sub> = 20V, I <sub>C</sub> = 10mA,
Current Gain-Bandwidth Product	f <sub>T</sub>	300		MHz	f = 100MHz
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0V, I_C = 100\mu A,$
SWITCHING CHARACTERISTICS					$R_S = 1.0k\Omega$ , f = 1.0kHz
Delay Time	t <sub>d</sub>	_	35	ns	V <sub>CC</sub> = 3.0V, I <sub>C</sub> = 10mA,
Rise Time	ta tr	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$
Storage Time	t <sub>s</sub>		200	ns	$V_{BE(0ff)} = 0.0V, B = 1.0mA$
Fall Time			50	-	
Fall Lime	tf	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

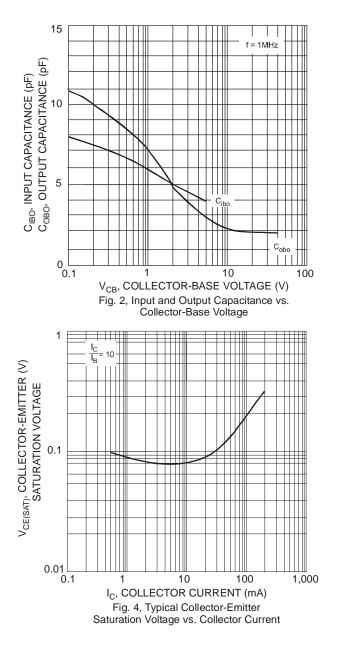
Note:

7. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

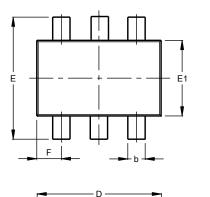


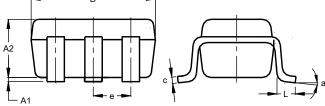




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

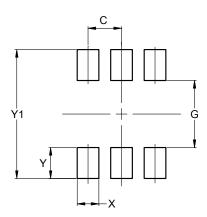




SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	1.00				
b	0.10	0.30	0.25				
С	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	).650 B	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All	Dimen	sions	in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated

www.diodes.com

# **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Diodes Incorporated: MMDT3904-7-F